

U.S. Department of Commerce, Patent and Trademark INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) (Form PTO-1449)			Atty. Docket No. SNDK.352US0 Applicant(s) Lutze et al.		Application No. 10/799,060 Conf. No. 6740		
			Filing Date March 12, 2004		Art Group 2818		
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Examiner	<i>M. H. Lutze</i>	Date Considered					<i>11/28/05</i>
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